

# ■ Development Project of “**New Ti Precursors**”

## □ Target : **TiO<sub>2</sub>**

Code Name	<b>TCTi-2</b>
<b>1) TGA<sub>1/2</sub> (°C)</b>	150
<b>Residual mass (%)</b>	< 1%
<b>2) DSC (°C)</b>	264

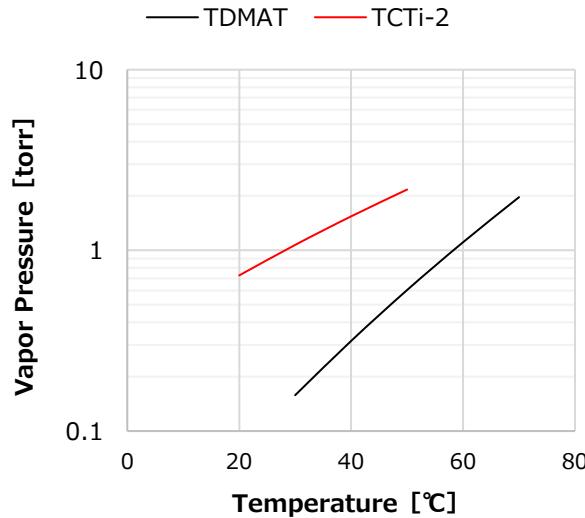
**1) TGA (Thermogravimetric Analysis) : Volatility property of precursor**

- TGA<sub>1/2</sub> (°C) : Temperature at 50% vaporization (low temperature → high volatility)

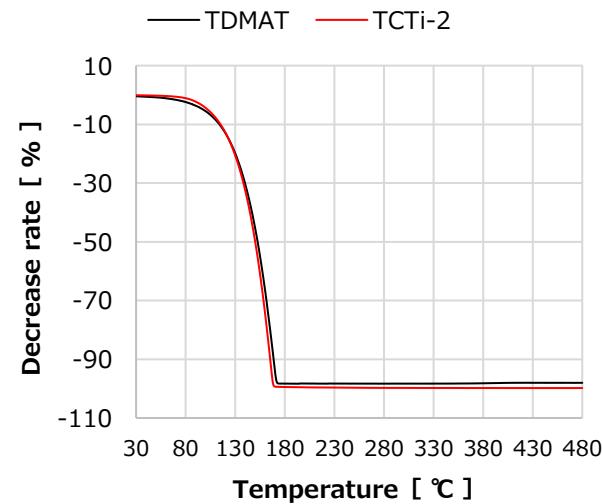
- Residual mass (%) : Residue mass after vaporization (low value → good thermal stability)

**2) DSC (Differential Scanning Calorimetry) : Decomposition temperature of precursor**

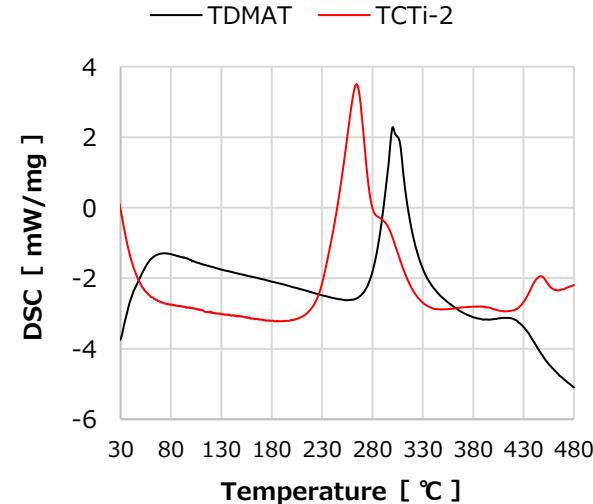
## ■ Vapor Pressure curve



## ■ TGA curve



## ■ DSC curve

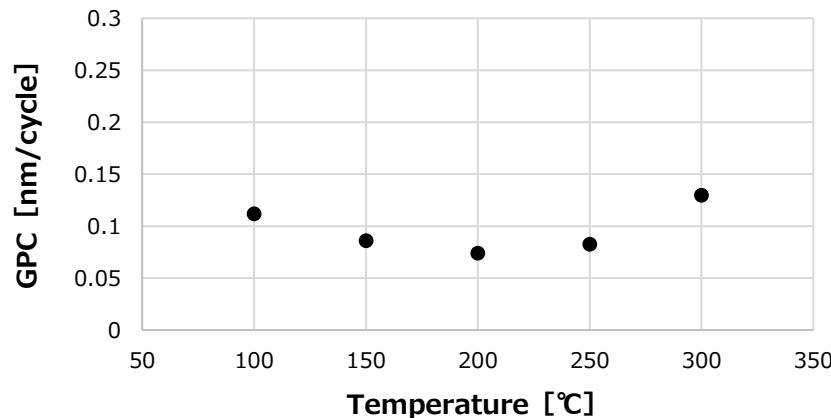


# ■ Development Project of “**New Ti Precursors**”

## □ ALD evaluation about TCTi-2

substrate	Si
reactant	H <sub>2</sub> O
ALD window	150~250°C
Intensity - XPS -	C [atm%] <b>&lt; 0.01</b>
	N [atm%] <b>&lt; 0.01</b>

### ■ substrate Temp. vs GPC



### ■ substrate Temp. vs refractive index (633nm)

